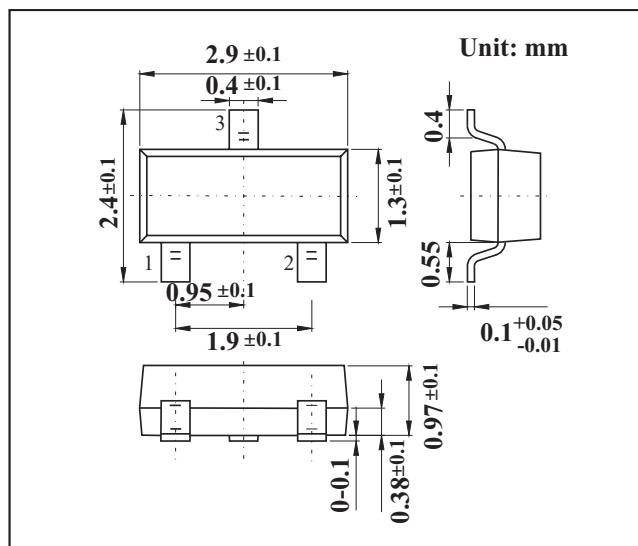


SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Supply Voltage	V _{CC}	-50	V
Input Voltage	V _{IN}	-30 ~ +5	V
Output Current	I _O	-100	mA
Power Dissipation	P _D	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

Mosfet Electrical Characteristics TA=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	V _{I(off)}	V _{CC} =-5V, I _O =-100µA	-0.5			V
	V _{I(on)}	V _O =-0.3V, I _O =-5mA			-1.3	V
Output voltage	V _{O(on)}	I _O /I _I =-5mA/-0.25mA			-0.3	V
Input current	I _I	V _I =-5V			-1.8	mA
Output current	I _{O(off)}	V _{CC} =-50V, V _I =0			-0.5	µA
DC current gain	G _I	V _O =-5V, I _O =-10mA	80			
Input resistance	R _I		3.29	4.7	6.11	kΩ
Resistance ratio	R ₂ /R ₁		8	10	12	
Transition frequency	f _T	V _O =-10V, I _O =-5mA, f=100MHz		250		MHz

RATINGS AND CHARACTERISTIC CURVES

